TOSHIBA Bi-CMOS Digital Integrated Circuit Silicon Monolithic

## **TB2903HQ**

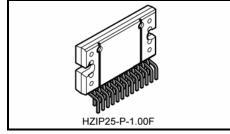
#### Maximum Power 47 W BTL x 4-ch Audio Power IC

The TB2903HQ is 4-ch BTL audio amplifier for car audio applications.

This IC can generate higher power:  $P_{OUT}$  MAX = 47 W as it includes the pure complementary P-ch and N-ch DMOS output stage.

It is designed to yield low distortion ratio for 4-ch BTL audio power amplifier, built-in standby function, muting function, and various kinds of protectors.

Additionally, Off-set detector is built in.



Weight: 7.7 g (typ.)

#### **Features**

- High power output
  - :  $P_{OUT} MAX (1) = 47 W (typ.)$

 $(V_{CC} = 14.4 \text{ V}, f = 1 \text{ kHz}, \text{JEITA max}, R_L = 4 \Omega)$ 

: POUT MAX (2) = 43 W (typ.)

 $(V_{CC} = 13.7 \text{ V}, f = 1 \text{ kHz}, \text{JEITA max}, R_L = 4 \Omega)$ 

:  $P_{OUT}(1) = 29 \text{ W (typ.)}$ 

 $(V_{CC} = 14.4 \text{ V}, f = 1 \text{ kHz}, THD = 10\%, R_L = 4 \Omega)$ 

: POUT(2) = 25 W (typ.)

 $(V_{CC} = 13.2 \text{ V}, f = 1 \text{ kHz}, THD = 10\%, RL = 4 \Omega)$ 

• Low distortion ratio: THD = 0.015% (typ.)

$$(V_{\rm CC}=13.2~\rm V,~f=1~\rm kHz,~P_{\rm OUT}=5~\rm W,~R_{\rm L}=4~\Omega)$$

• Low noise:  $V_{NO} = 90 \,\mu V_{rms}$  (typ.)

(V<sub>CC</sub> = 13.2 V, 
$$R_g$$
 = 0  $\Omega$ , BW = 20 Hz~20 kHz,  $R_L$  = 4  $\Omega$ )

- Built-in standby switch function (pin 4)
- Built-in muting function (pin 22)
- Built-in Off-set detection function (pin 25)
- Built-in various protection circuits:

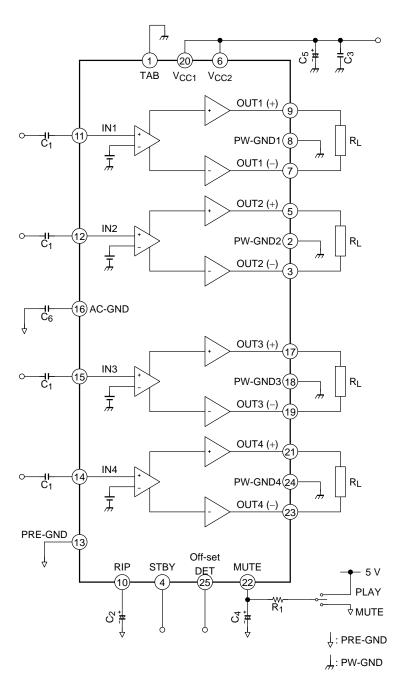
Thermal shut down, overvoltage, out to GND, out to VCC, out to out short

- Operating supply voltage:  $V_{CC (opr)} = 9 \sim 18 \text{ V (RL} = 4 \Omega)$ 
  - Note 1: Since this device's pins have a low withstanding voltage, please handle it with care.
  - Note 2: Install the product correctly. Otherwise, it may result in break down, damage and/or degradation to the product or equipment.
  - Note 3: These protection functions are intended to avoid some output short circuits or other abnormal conditions temporarily. These protect functions do not warrant to prevent the IC from being damaged.

    In case of the product would be operated with exceeded guaranteed operating ranges, these protection features may not operate and some output short circuits may result in the IC being damaged.

2004-07-25

## **Block Diagram**



Note4: Some of the functional blocks, circuits, or constants in the block diagram may be omitted or simplified for explanatory purpose.

#### **Caution and Application Method**

(Description is made only on the single channel.)

#### 1. Voltage Gain Adjustment

This IC has no NF (negative feedback) Pins. Therefore, the voltage gain can not be adjusted, but it makes the device a space and total costs saver.

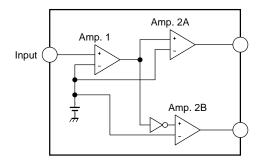


Figure 1 Block Diagram

$$\label{eq:GV1} \begin{split} & \text{The voltage gain of amp.1} & & \text{$:$GV$$1} = 0 dB \\ & \text{The voltage gain of amp.2A, B} & & \text{$:$GV$$2} = 20 dB \end{split}$$

The voltage gain of BTL connection: GV (BTL) = 6dB

Therefore, the total voltage gain is decided by expression below.

$$G_V = G_{V1} + G_{V2} + G_{V (BTL)} = 0 + 20 + 6 = 26dB$$

## 2. Standby SW Function (pin 4)

By means of controlling pin 4 (standby pin) to High and Low, the power supply can be set to ON and OFF. The threshold voltage of pin 4 is set at about 3VBE (typ.), and the power supply current is about 2  $\mu A$  (typ.) in the standby state.

#### Control Voltage of Pin 4: V<sub>SB</sub>

Standby	Power	V <sub>SB</sub> (V)
ON	OFF	0~1.5
OFF	ON	3.5~6 V

When changing the time constant of pin 4, check the pop noise.

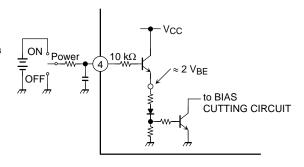


Figure 2 With pin 4 set to High, Power is turned ON

#### **Advantage of Standby SW**

- (1) Since VCC can directly be controlled to ON or OFF by the microcomputer, the switching relay can be omitted
- (2) Since the control current is microscopic, the switching relay of small current capacity is satisfactory for switching.

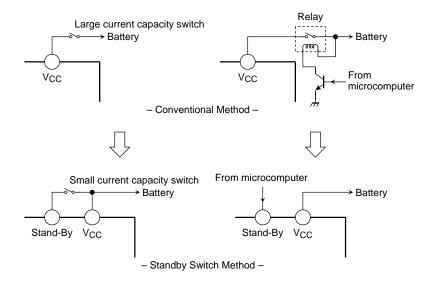


Figure 3

#### 3. Muting Function (pin 22)

Audio muting function is enabled when pin 22 is Low. When the time constant of the muting function is determined by  $R_1$  and  $C_4$ , it should take into account the pop noise. The pop noise which is generated when the power or muting function is turned ON/OFF will vary according to the time constant. (Refer to Figure 4 and Figure 5.)

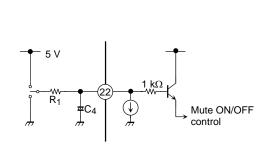
The pin 22 is designed to operate off 5 V.

Moreover, this terminal (pin 22) serves as the source switch of current of an internal mute circuit. And it is designed so that the discharge current of this terminal (pin 22) may serve as 200  $\mu$ A. The outside pull-up resistor  $R_1$  is determind on the basic of this value.

ex) When control voltage is changed in to 6 V from 5 V.

$$6~V/5~V\times47~k=56~k$$

To obtain enough mute attenuation, a series resistor,  $R_{1}$  at pin 22 should be 47  $k\Omega$  or more.



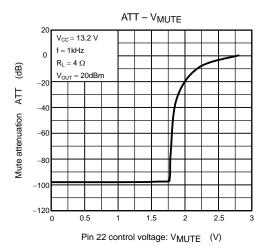


Figure 4 Muting Function

Figure 5 Mute Attenuation – V<sub>MUTE</sub> (V)

#### 4. Off-set detection function

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In case of Appearing output offset voltage by Generating a Large Leakage Current on the input Capacitor etc.

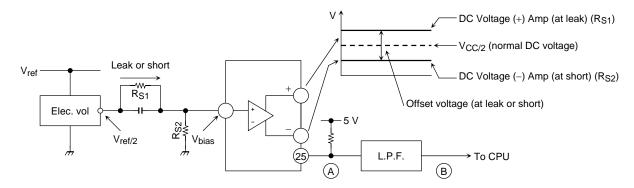


Figure 6 Application and Detection Mechanism

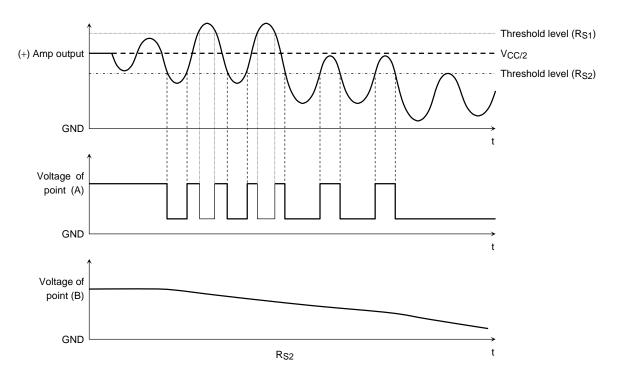


Figure 7 Wave Form

#### 5. Pop Noise Suppression

Since the AC-GND pin (pin 16) is used as the NF pin for all amps, the ratio between the input capacitance (C1) and the AC-to-GND capacitance (C6) should be 1:4.

Also, if the power is turned OFF before the C1 and C6 batteries have been completely charged, pop noise will be generated because of the DC input unbalance.

To counteract the noise, it is recommended that a longer charging time be used for C2 as well as for C1 and C6. Note that the time which audio output takes to start will be longer, since the C2 makes the muting time (the time from when the power is turned ON to when audio output starts) is fix.

The pop noise which is generated when the muting function is turned ON/OFF will vary according to the time constant of C4.

The greater the capacitance, the lower the pop noise. Note that the time from when the mute control signal is applied to C4 to when the muting function is turned ON/OFF will be longer.

#### 6. External Component Constants

Component	Recommended		Eff		
Name Value		Purpose	Lower than recommended value	Higher than recommended value	Notes
C1	0.22 μF	To eliminate DC	Cut-off frequency is reduced		Pop noise is generated when V <sub>CC</sub> is ON
C2	10 μF	To reduce ripple	Powering ON/OFF is faster	Powering ON/OFF takes longer	
C3	0.1 μF	To provide sufficient oscillation margin	Reduces noise and provides s		
C4	1 μF	To reduce pop noise	High pop noise. Duration until muting function is turned ON/OFF is short	on is turned muting function is turned	
C5	3900 μF	Ripple filter	Power supply ripple filtering		
C6	1 μF	NF for all outputs	Pop noise is suppressed when	Pop noise is generated when V <sub>CC</sub> is ON	

Note5: If recommended value is not used.

#### **Maximum Ratings (Ta = 25°C)**

Characteristics	Symbol	Rating	Unit
Peak supply voltage (0.2 s)	V <sub>CC</sub> (surge)	50	V
DC supply voltage	V <sub>CC</sub> (DC)	25	V
Operation supply voltage	V <sub>CC</sub> (opr)	18	V
Output current (peak)	I <sub>O (peak)</sub>	9	Α
Power dissipation	P <sub>D</sub> (Note 6)	125	W
Operation temperature	T <sub>opr</sub>	-40~85	°C
Storage temperature	T <sub>stg</sub>	-55~150	°C

Note 6: Package thermal resistance  $\theta_{j-T} = 1^{\circ}\text{C/W}$  (typ.) (Ta = 25°C, with infinite heat sink)

The absolute maximum ratings of a semiconductor device are a set of specified parameter values, which must not be exceeded during operation, even for an instant. If any of these rating would be exceeded during operation, the device electrical characteristics may be irreparably altered and the reliability and lifetime of the device can no longer be guaranteed. Moreover, these operations with exceeded ratings may cause break down, damage and/or degradation to any other equipment. Applications using the device should be designed such that each maximum rating will never be exceeded in any operating conditions. Before using, creating and/or producing designs, refer to and comply with the precautions and conditions set forth in this documents.

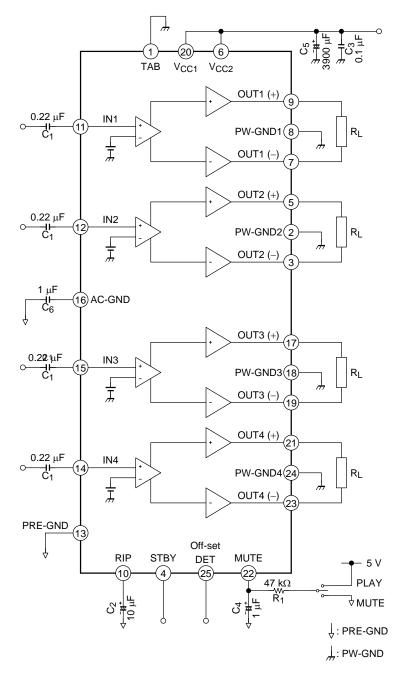
# Electrical Characteristics (unless otherwise specified, $V_{CC}$ = 13.2 V, f = 1 kHz, $R_L$ = 4 $\Omega$ , Ta = 25°C)

Characteristics	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Quiescent current	Icca	_	$V_{IN} = 0$	_	200	400	mA
Output power	P <sub>OUT</sub> MAX (1)	_	V <sub>CC</sub> = 14.4 V, max POWER		47	_	
	P <sub>OUT</sub> MAX (2)	_	V <sub>CC</sub> = 13.7 V, max POWER		43	_	w
	P <sub>OUT</sub> (1)	_	V <sub>CC</sub> = 14.4 V, THD = 10%	_	29	_	VV
	P <sub>OUT</sub> (2)	_	THD = 10%	23	25	_	
Total harmonic distortion	THD	_	P <sub>OUT</sub> = 5 W	_	0.015	0.15	%
Voltage gain	G <sub>V</sub>	_	V <sub>OUT</sub> = 0.775 Vrms	24	26	28	dB
Voltage gain ratio	ΔG <sub>V</sub>	_	V <sub>OUT</sub> = 0.775 Vrms	-1.0	0	1.0	dB
Output noise voltage	V <sub>NO</sub> (1)	_	Rg = 0 Ω, DIN45405	_	100	_	μVrms
	V <sub>NO</sub> (2)	_	Rg = 0 Ω, BW = 20 Hz~20 kHz		90	200	
Ripple rejection ratio	R.R.	_	$\begin{aligned} f_{rip} &= 100 \text{ Hz},  R_g = 620  \Omega \\ V_{rip} &= 0.775  \text{Vrms} \end{aligned}$	50	60	_	dB
Cross talk	C.T.	_	$\begin{array}{l} \text{R}_{\text{g}} = 620~\Omega\\ \text{V}_{\text{OUT}} = 0.775~\text{Vrms} \end{array}$	_	70	_	dB
Output offset voltage	Voffset	_	_	-150	0	150	mV
Input resistance	R <sub>IN</sub>	_	_	_	90	_	kΩ
Standby current	I <sub>SB</sub>	_	Standby condition		2	10	μА
Standby control voltage	V <sub>SB</sub> H	_	POWER: ON	3.5	_	6.0	V
	V <sub>SB</sub> L	_	POWER: OFF	0	_	1.5	V
Mute control voltage	V <sub>M</sub> H	_	MUTE: OFF	3.0	_	6.0	V
	V <sub>M</sub> L	_	MUTE: ON, $R_1 = 47 \text{ k}\Omega$	0	_	0.5	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
Mute attenuation	ATT M	_	MUTE: ON V <sub>OUT</sub> = 7.75 Vrms→Mute: OFF	80	90	_	dB

#### Offset detection

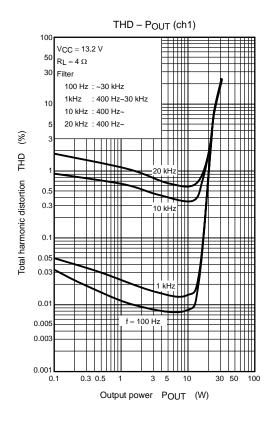
Detection threshold voltage	Voff-set		Rpull-up = 47 k $\Omega$ , +V = 5.0V Based on output DC voltage	±1.0	±1.5	±2.0	V
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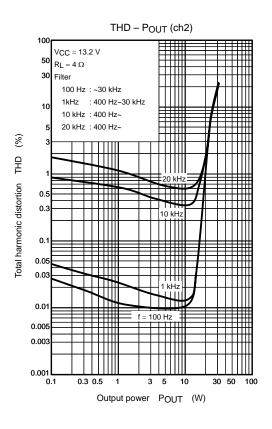
## **Test Circuit**

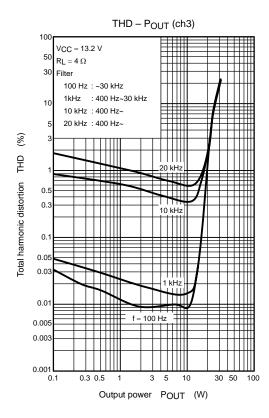


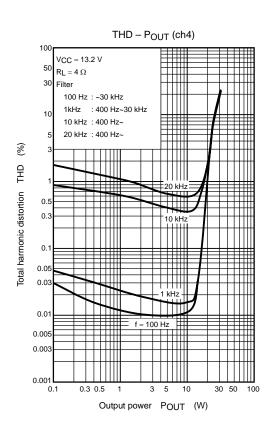
Components in the test circuits are only used to obtain and confirm the device characteristics.

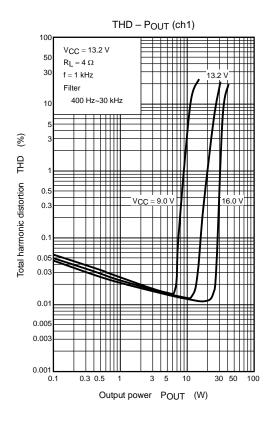
These components and circuits do not warrant to prevent the application equipment from malfunction or failure.

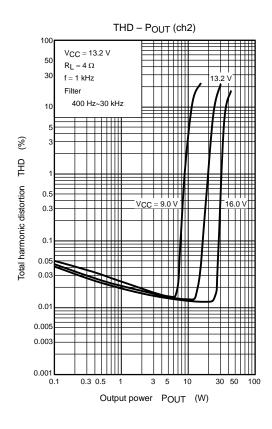


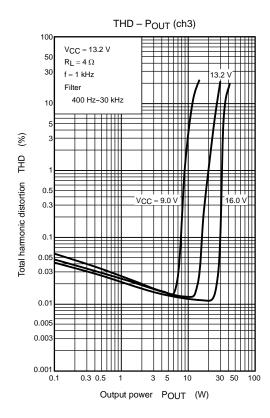


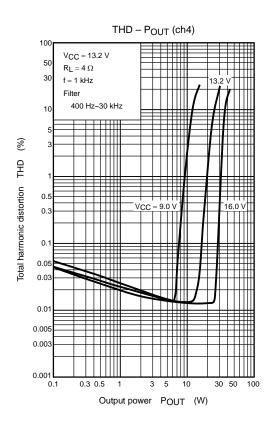


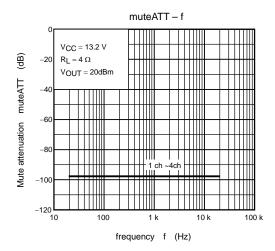


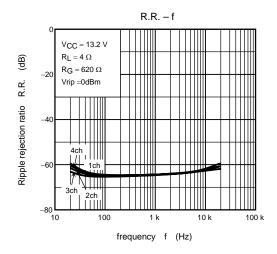


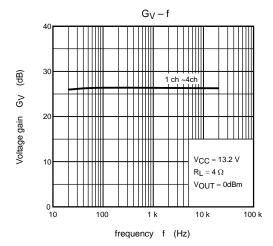


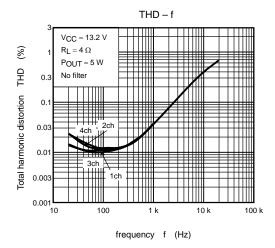


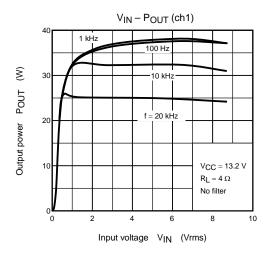


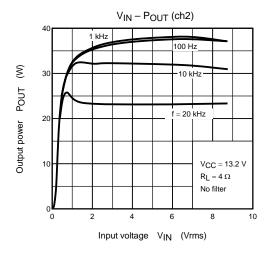


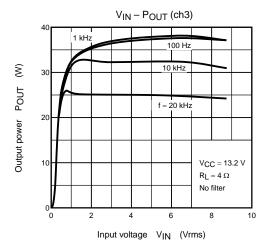


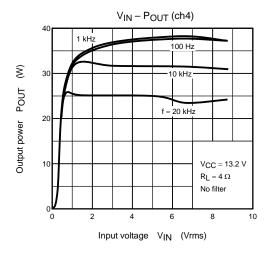


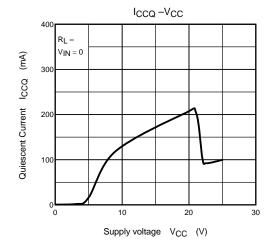


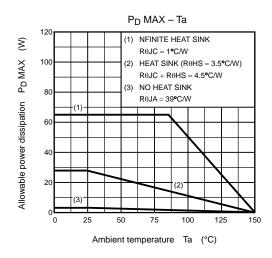


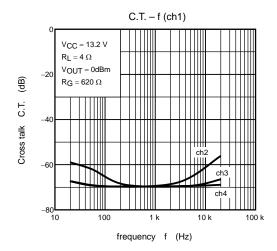


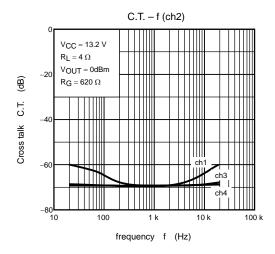


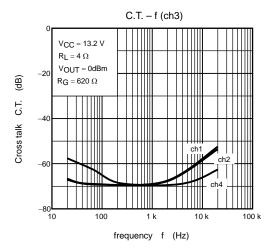


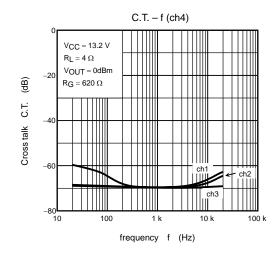


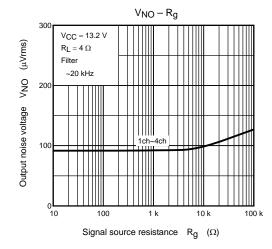


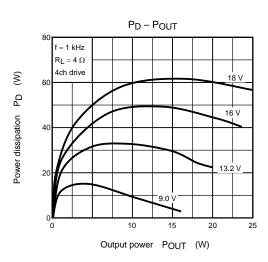






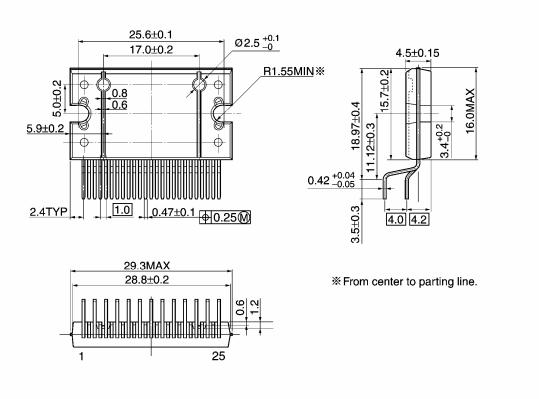






## **Package Dimensions**

HZIP25-P-1.00F Unit: mm



Weight: 7.7 g (typ.)

About solderability, following conditions were confirmed

- Solderability
  - (1) Use of Sn-63Pb solder Bath
    - solder bath temperature = 230°C
    - · dipping time = 5 seconds
    - · the number of times = once
    - · use of R-type flux
  - (2) Use of Sn-3.0Ag-0.5Cu solder Bath
    - solder bath temperature = 245°C
    - · dipping time = 5 seconds
    - · the number of times = once
    - · use of R-type flux

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